

First Named Inventor	Leonard Forbes	INFORMATION DISCLOSURE STATEMENT FORM PTO-1449
Serial No.	10/682,590	
Filing Date	October 9, 2003	
Group Art Unit	2811	
Examiner Name	Unknown	
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Attorney Docket No.	400.257US01	
Title: FULLY DEPLETED SILICON-ON-INSULATOR CMOS LOGIC		Sheet 1 of 7

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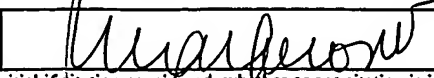
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